DIODE MODULE (F.R.D.)

DD250GB







Power Diode Module **DD250GB** series are designed for various rectifier circuits. **DD250GB** has two diode chips connected in series in a package and the mounting base is electrically isolated from elements for simple heatsink construction. Wide voltage rating

up to 800V is available for various input voltage.

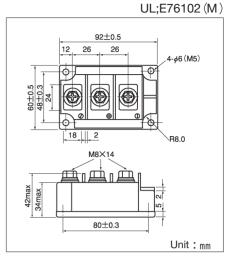
• Isolated mounting base

- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

(Applications)

Various rectifiers, Bettery chargers, DC motor drives





Maximum Ratings

(Tj=25°C)

Symbol	Sumbol	Ratings		
	Symbol	DD250GB40	DD250GB80	Unit
VRRM	Repetitive Peak Reverse Voltage	400	800	V
VRSM	Non-Repetitive Peak Reverse Voltage	480	960	V

Symbol	Sy	mbol	Conditions	Ratings	Unit
IF (AV)	Average Forward Current		Single phase, half wave, 180°C conduction, Tc: 98°C	250	Α
IF (RMS)	R.M.S. Forward Current		Single phase, half wave, 180°C conduction, Tc: 98°C	390	Α
IFSM	Surge Forward Current		½ cycle, 50/60Hz, peak value, non-repetitive	5000/5500	Α
l²t	I²t Value for one cycle of surge current		Value for one cycle of surge current	125000	A ² S
Tj	Operating Junction Temperature			−40∼+150	ي ش
Tstg	Storage Temperature			−40∼+125	℃
Viso	Isolation Breakdown Voltage (R.M.S.)		A.C. 1 minute	2500	V
	Mounting	Mounting (M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)	N·m
	Torque	Terminal (M8)	Recommended Value 8.8~10 (90~105)	11 (115)	(kgf·cm)
	Mass		Typical Value	510	g

■Electrical Characteristics

Symbol	Symbol	Conditions	Ratings			Unit
		Conditions		Тур.	Max.	Offit
IRRM	Repetitive Peak Reverse Current	Tj=150℃ at VRRM			50	mA
VFM	Forward Voltage Drop	Tj=25°C, IFM=750A, Inst. measurement			1.45	V
Rth (j-c)	Thermal Impedance	Junction to case			0.14	°C/W









